

# 2SK2553(L), 2SK2553(S)

Silicon N Channel MOS FET  
High Speed Power Switching

REJ03G1015-1000  
(Previous: ADE-208-357H)  
Rev.10.00  
Sep 07, 2005

## Application

High speed power switching

## Features

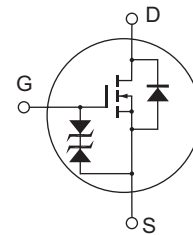
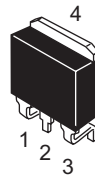
- Low on-resistance
- $R_{DS(on)} = 7 \text{ m}\Omega$  typ.
- High speed switching
- 4 V gate drive device can be driven from 5 V source

## Outline

RENESAS Package code: PRSS0004AE-A  
(Package name: LDBPAK(L))



RENESAS Package code: PRSS0004AE-B  
(Package name: LDBPAK(S)-(1))



1. Gate
2. Drain
3. Source
4. Drain

## Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{DSS}$	60	V
Gate to source voltage	$V_{GSS}$	±20	V
Drain current	$I_D$	50	A
Drain peak current	$I_{D(pulse)}$ <sup>Note 1</sup>	200	A
Body to drain diode reverse drain current	$I_{DR}$	50	A
Avalanche current	$I_{AP}$ <sup>Note 3</sup>	45	A
Avalanche energy	$E_{AR}$ <sup>Note 3</sup>	174	mJ
Channel dissipation	$P_{ch}$ <sup>Note 2</sup>	75	W
Channel temperature	$T_{ch}$	150	°C
Storage temperature	$T_{stg}$	-55 to +150	°C

Notes: 1.  $PW \leq 10 \mu s$ , duty cycle  $\leq 1\%$ 2. Value at  $T_c = 25^\circ C$ 3. Value at  $T_{ch} = 25^\circ C$ ,  $R_g \geq 50 \Omega$ 

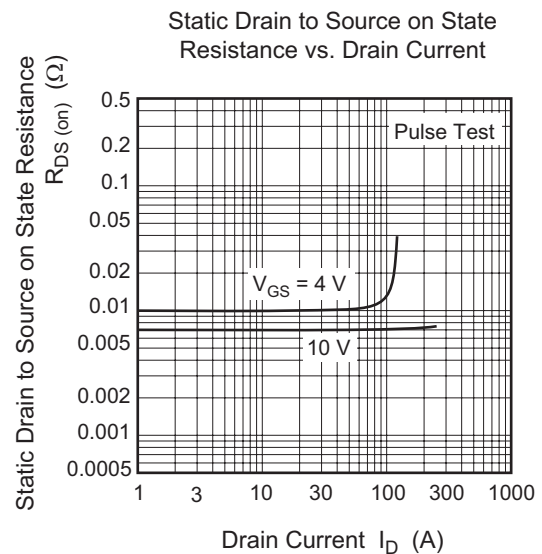
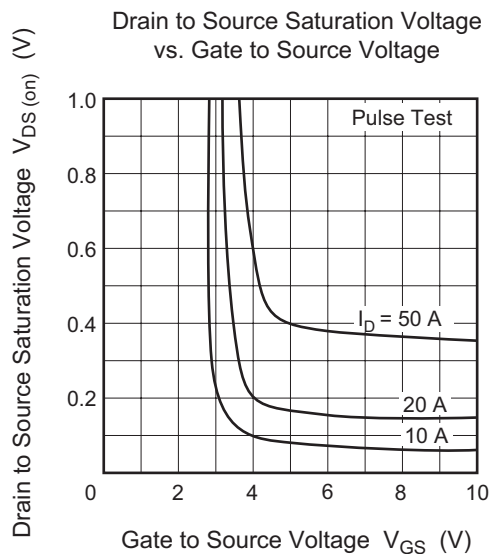
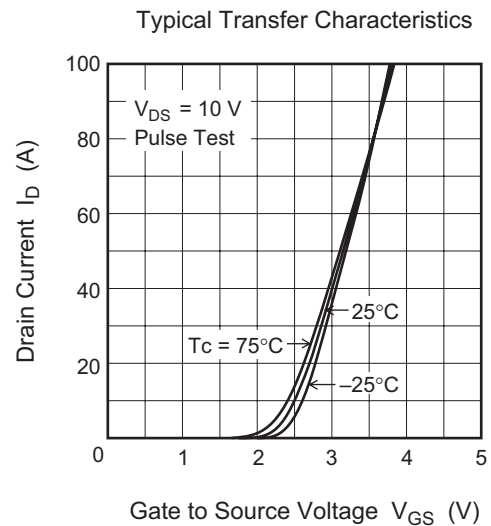
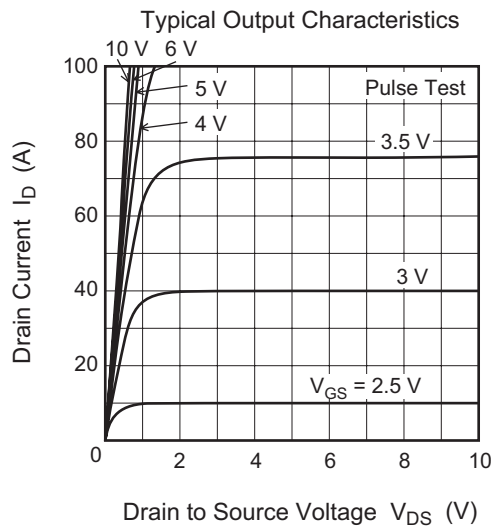
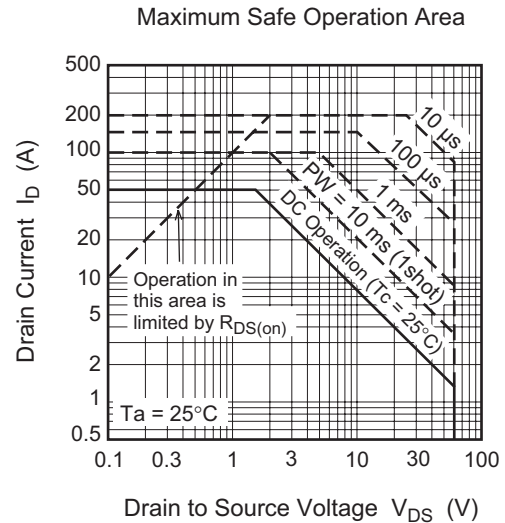
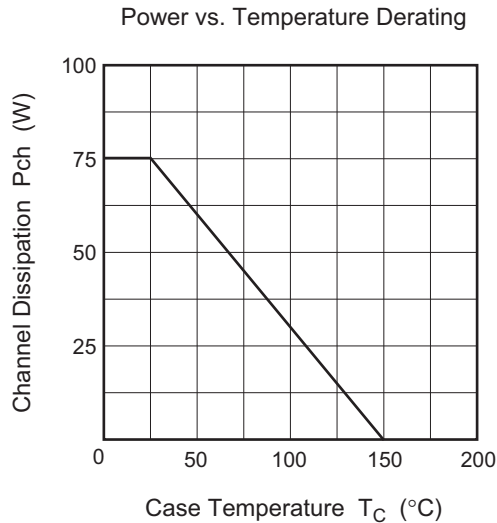
## Electrical Characteristics

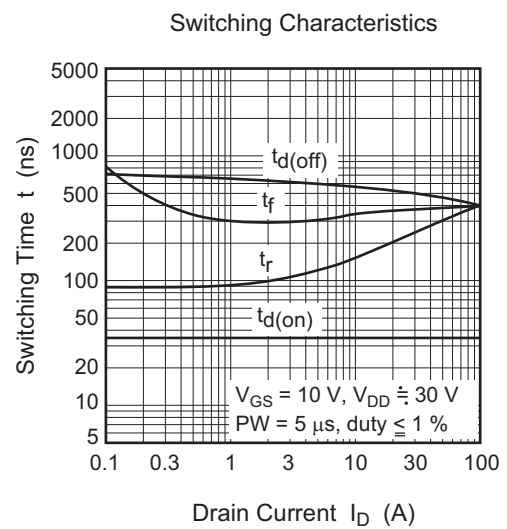
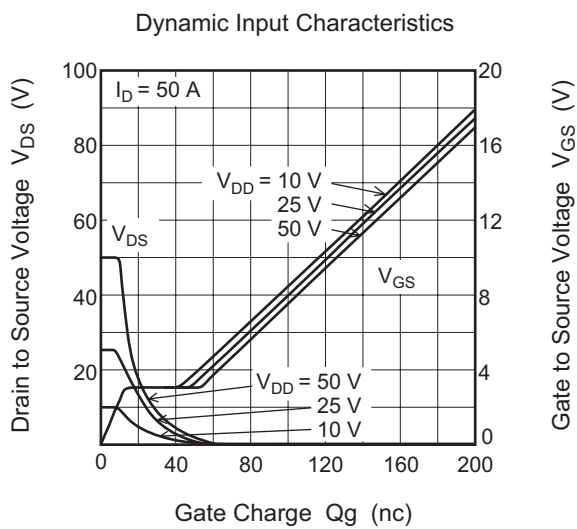
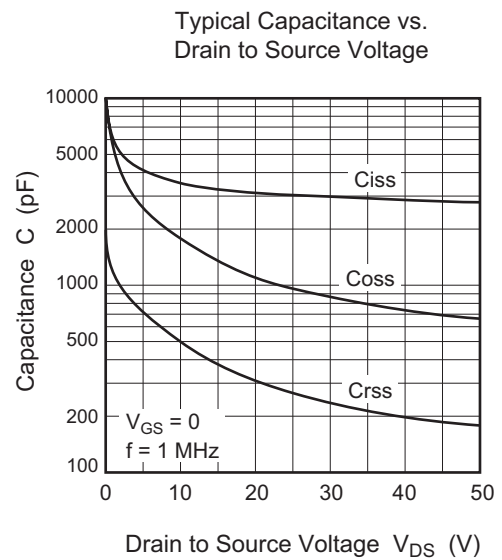
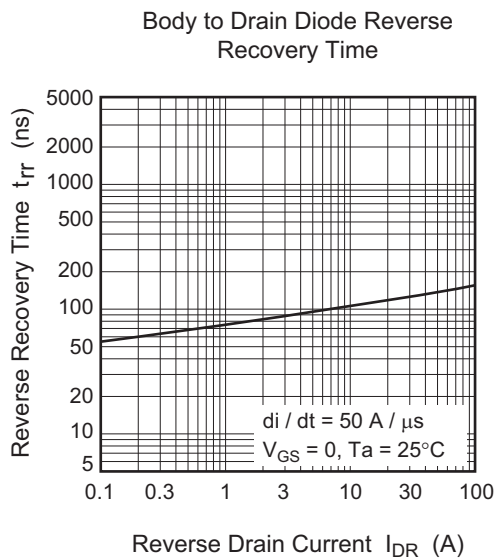
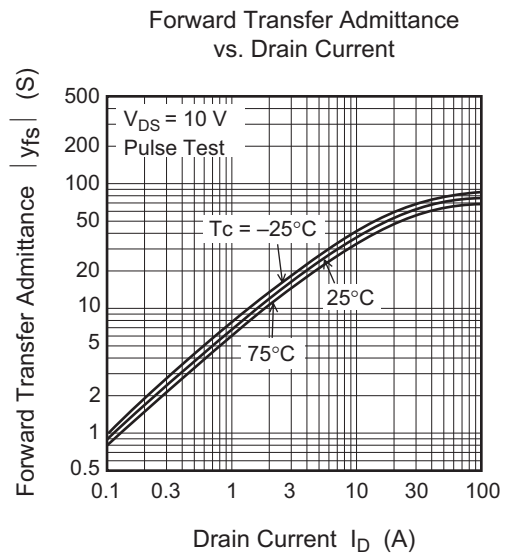
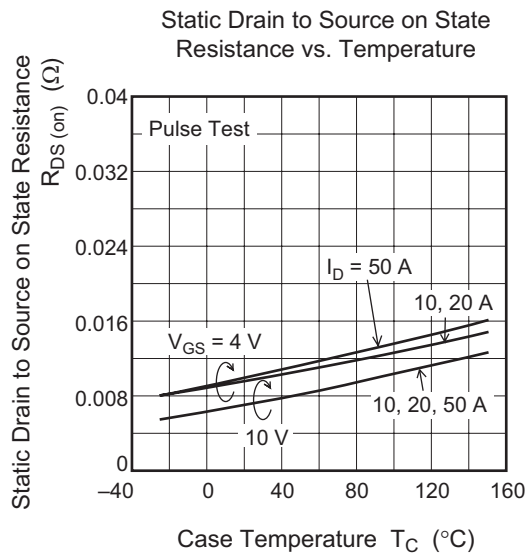
(Ta = 25°C)

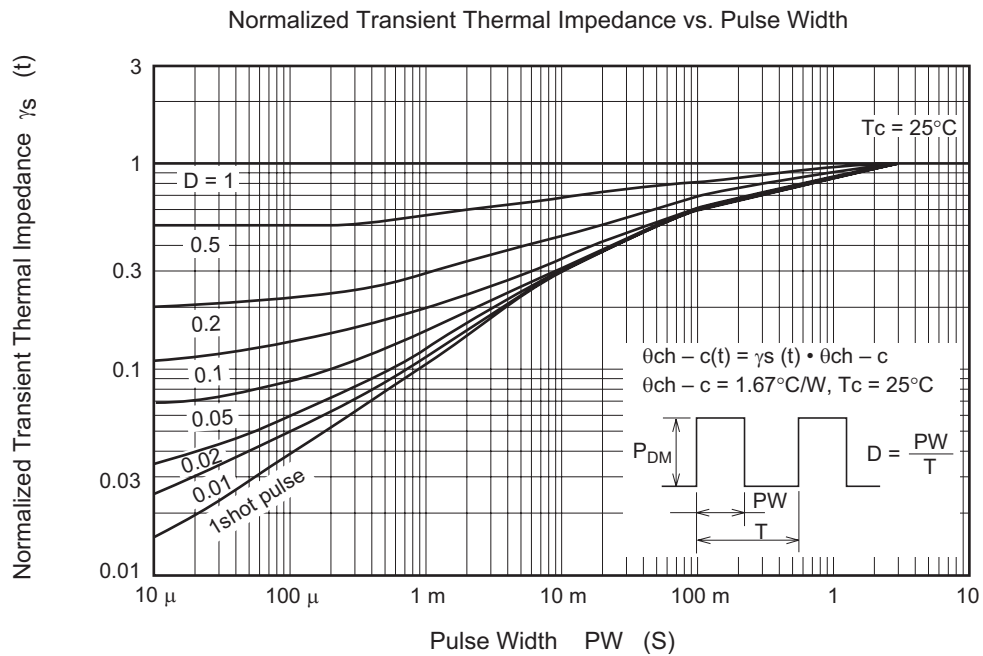
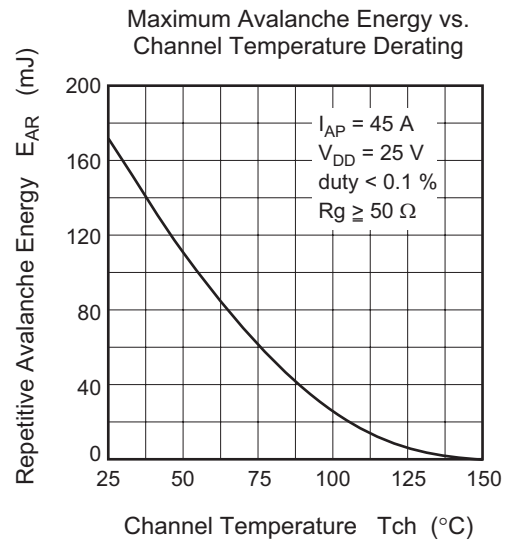
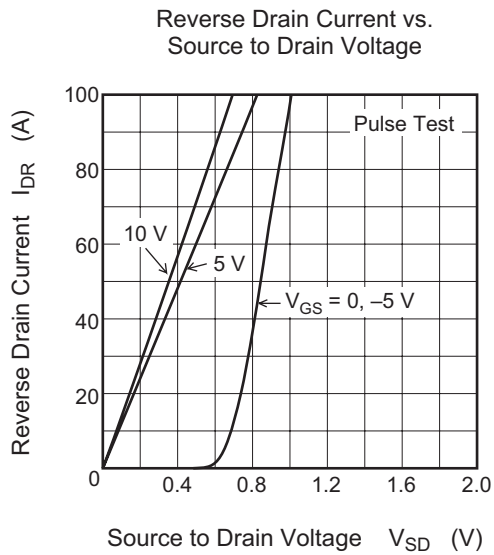
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	60	—	—	V	$I_D = 10 \text{ mA}$ , $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	—	—	V	$I_G = \pm 100 \mu A$ , $V_{DS} = 0$
Gate to source leak current	$I_{GSS}$	—	—	±10	μA	$V_{GS} = \pm 16 \text{ V}$ , $V_{DS} = 0$
Zero gate voltage drain current	$I_{DSS}$	—	—	10	μA	$V_{DS} = 60 \text{ V}$ , $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	—	2.0	V	$I_D = 1 \text{ mA}$ , $V_{DS} = 10 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	7	10	mΩ	$I_D = 25 \text{ A}$ , $V_{GS} = 10 \text{ V}$ <sup>Note 4</sup>
		—	10	16	mΩ	$I_D = 25 \text{ A}$ , $V_{GS} = 4 \text{ V}$ <sup>Note 4</sup>
Forward transfer admittance	$ y_{fs} $	35	55	—	S	$I_D = 25 \text{ A}$ , $V_{DS} = 10 \text{ V}$ <sup>Note 4</sup>
Input capacitance	$C_{iss}$	—	3550	—	pF	$V_{DS} = 10 \text{ V}$ , $V_{GS} = 0$ , $f = 1 \text{ MHz}$
Output capacitance	$C_{oss}$	—	1760	—	pF	
Reverse transfer capacitance	$C_{rss}$	—	500	—	pF	
Turn-on delay time	$t_{d(on)}$	—	35	—	ns	$I_D = 25 \text{ A}$ , $V_{GS} = 10 \text{ V}$ , $R_L = 1.2 \Omega$
Rise time	$t_r$	—	230	—	ns	
Turn-off delay time	$t_{d(off)}$	—	470	—	ns	
Fall time	$t_f$	—	360	—	ns	
Body to drain diode forward voltage	$V_{DF}$	—	0.85	—	V	$I_F = 50 \text{ A}$ , $V_{GS} = 0$
Body to drain diode reverse recovery time	$t_{rr}$	—	135	—	ns	$I_F = 50 \text{ A}$ , $V_{GS} = 0$ $di_F / dt = 50 \text{ A} / \mu s$

Note: 4. Pulse Test

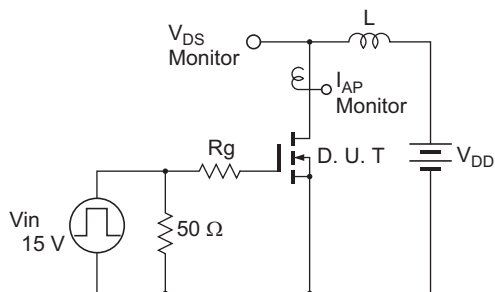
## Main Characteristics



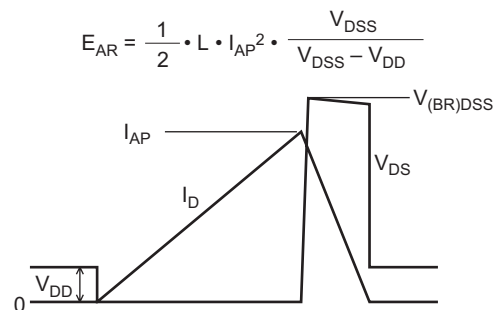


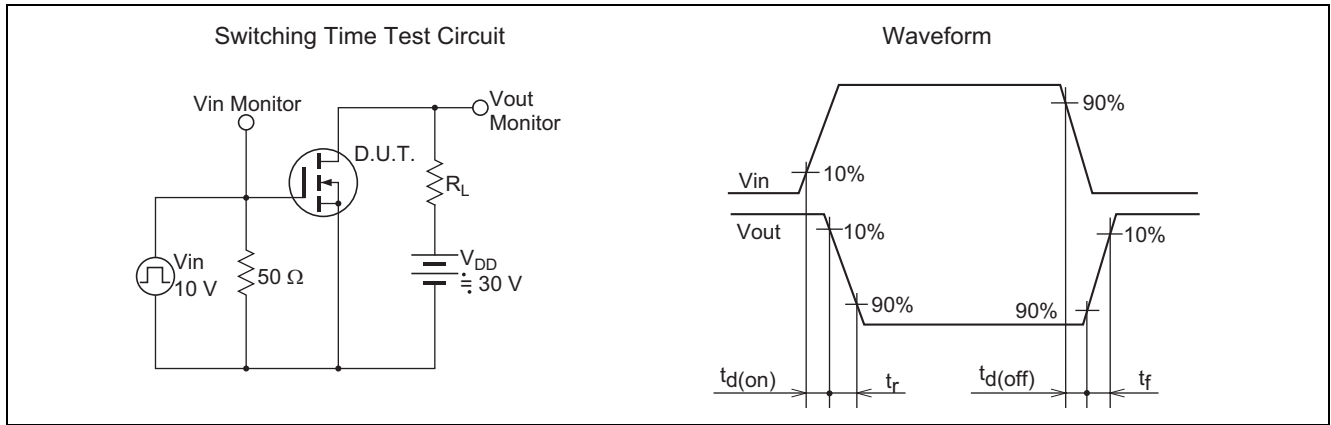


Avalanche Test Circuit

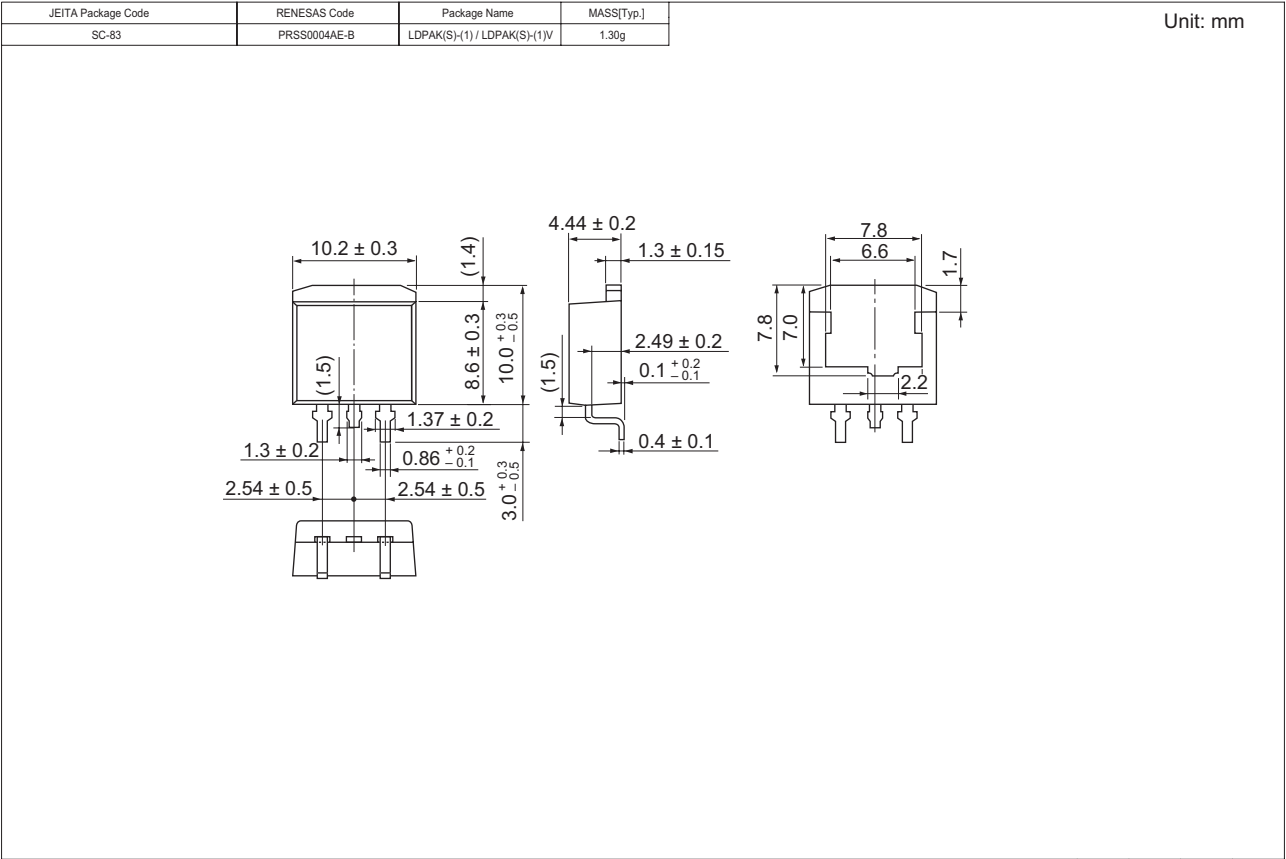
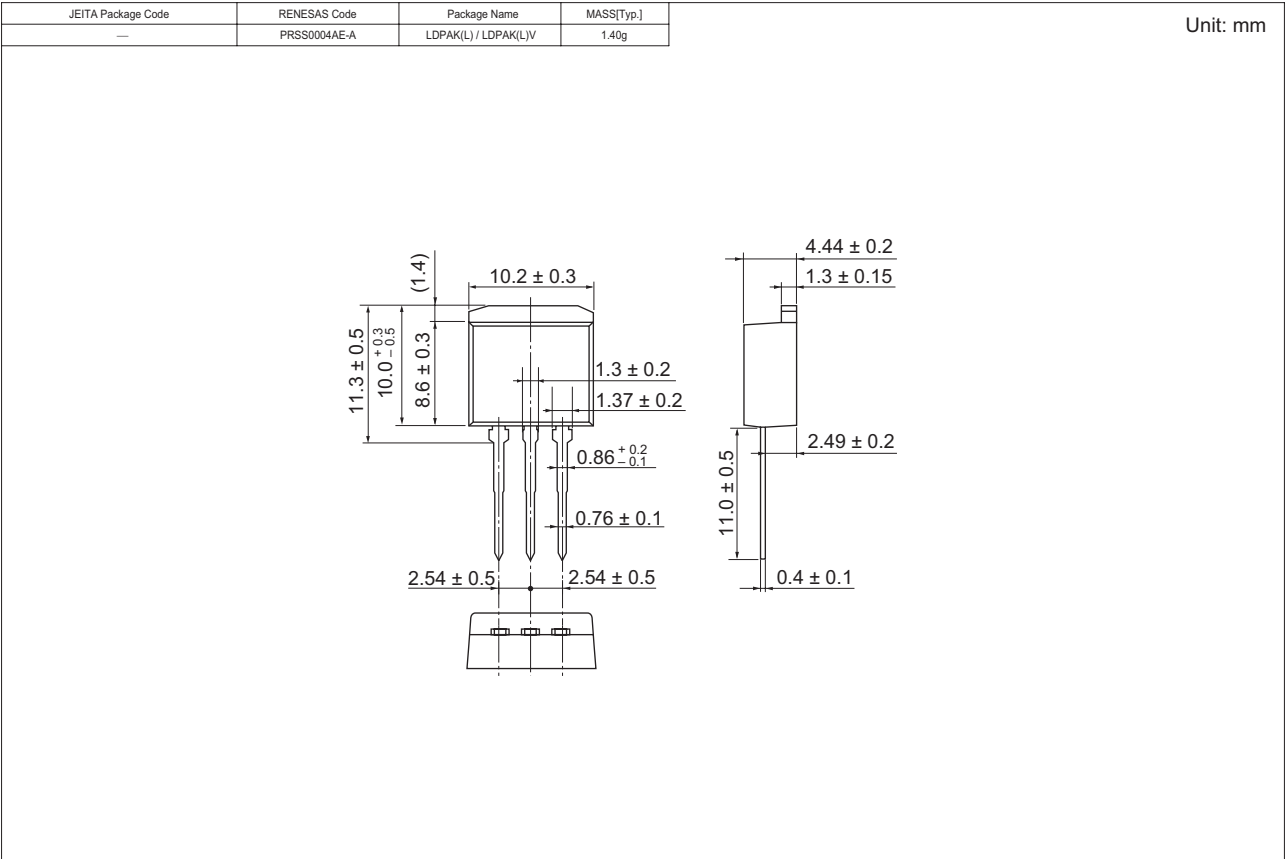


Avalanche Waveform





Package Dimensions



## Ordering Information

Part Name	Quantity	Shipping Container
2SK2553L-E	500 pcs	Box (Sack)
2SK2553STL-E	1000 pcs	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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